Zener Diodes, 40 Watt Peak Power

SOT-23 Dual Common Cathode Zeners

These dual monolithic silicon zener diodes are designed for applications requiring protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT–23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range 15 V, 27 V, 39 V
- Peak Power 40 W @ 1.0 ms (Bidirectional), per Figure 5 Waveform
- ESD Rating of Class 3B (exceeding 16 kV) per the Human Body Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V-O
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

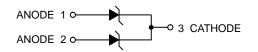


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SOT-23 CASE 318 STYLE 9



MARKING DIAGRAM



XXX = 15D, 27C or 39C M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]			
MMBZ15VDLT1G,	SOT-23	3,000 /			
SZMMBZ15VDLT1G	(Pb-Free)	Tape & Reel			
MMBZ15VDLT3G,	SOT-23	10,000 /			
SZMMBZ15VDLT3G	(Pb-Free)	Tape & Reel			
MMBZxxVCLT1G,	SOT-23	3,000 /			
SZMMBZxxVCLT1G	(Pb-Free)	Tape & Reel			
MMBZxxVCLT3G,	SOT-23	10,000 /			
SZMMBZxxVCLT3G	(Pb-Free)	Tape & Reel			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ T _L ≤ 25°C	P _{pk}	40	Watts
Total Power Dissipation on FR–5 Board (Note 2) @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

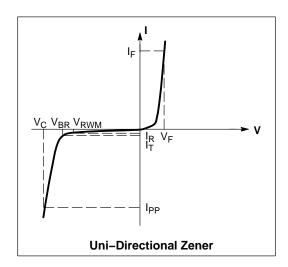
- 1. Nonrepetitive current pulse per Figure 5 and derate above T_A = 25°C per Figure 6.
- 2. $FR-5 = 1.0 \times 0.75 \times 0.62 \text{ in.}$
- 3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
V _{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA})$

				Breakdown Voltage			V _C @ I _{PP} (Note 5)			
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BI}	V _{BR} (Note 4) (V) @ I _T		@ I _T	V _C	I _{PP}	V_{BR}
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ15VDLT1G/T3G	15D	12.8	100	14.3	15	15.8	1.0	21.2	1.9	12

 $(V_F = 1.1 \text{ V Max } @ I_F = 200 \text{ mA})$

					Breakdown Voltage			V _C @ I _{PP} (Note 5)		
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BI}	(Note 4)	(V)	@ I _T	V _C	I _{PP}	V_{BR}
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ27VCLT1G/T3G	27C	22	50	25.65	27	28.35	1.0	38	1.0	26
MMBZ39VCLT1G/T3G	39C	31.2	50	37.05	39	40.95	1.0	55	0.76	35.3

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.

^{5.} Surge current waveform per Figure 5 and derate per Figure 6 *Include SZ-prefix devices where applicable.

TYPICAL CHARACTERISTICS

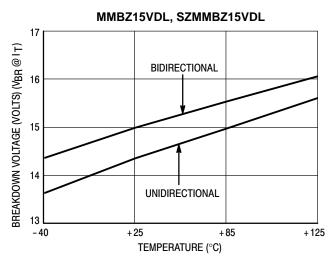


Figure 1. Typical Breakdown Voltage versus Temperature

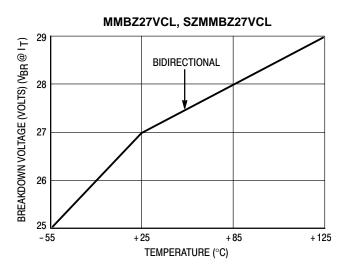


Figure 2. Typical Breakdown Voltage versus Temperature

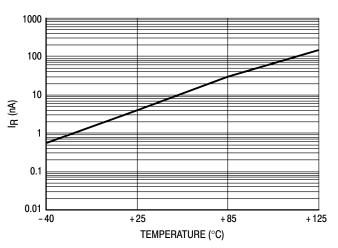


Figure 3. Typical Leakage Current versus Temperature

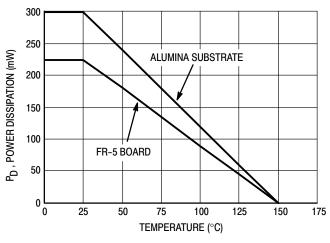


Figure 4. Steady State Power Derating Curve

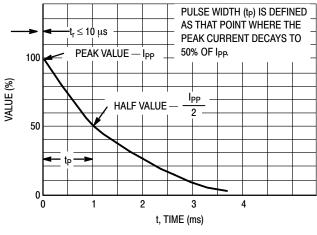


Figure 5. Pulse Waveform

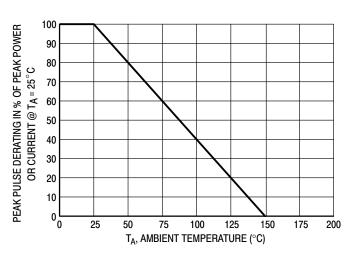


Figure 6. Pulse Derating Curve

TYPICAL APPLICATIONS

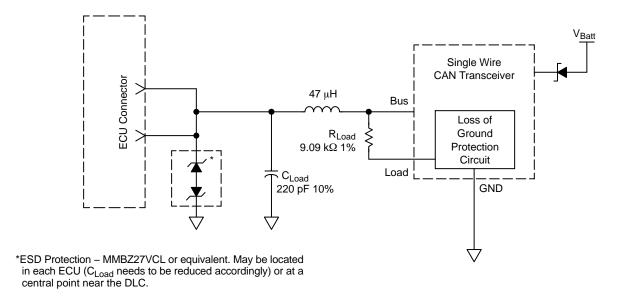
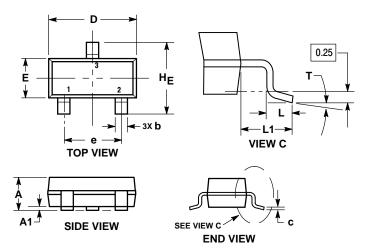


Figure 7. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 "Single Wire CAN Network for Vehicle Applications" specification (Figure 6, page 11). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AS**



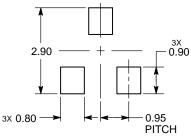
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

	M	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
T	0°	-	10°	0°	-	10°	

STYLE 9:

- PIN 1. ANODE 2. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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